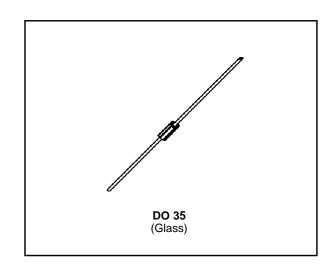
SMALL SIGNAL SCHOTTKY DIODES



DESCRIPTION

General purpose, metal to silicon diodes featuring very low turn-on voltage fast switching.

These devices have integrated protection against excessive voltage such as electrostatic discharges.

ABSOLUTE RATINGS (limiting values)

Symbol	Parameter	Value	Unit		
V_{RRM}	Repetitive Peak Reverse Voltage		30	V	
lF	Forward Continuous Current 7	200	mA		
I _{FRM}	Repetitive Peak Fordware Current	500	mA		
I _{FSM}	Surge non Repetitive Forward Current* t	4	Α		
P _{tot}	Power Dissipation*	200	mW		
T _{stg} T _j	Storage and Junction Temperature Range	- 65 to +150 - 65 to +125	ို့ လ		
TL	Maximum Temperature for Soldering during 10s at 4mm from Case 230				

THERMAL RESISTANCE

Symbol	Test Conditions	Value	Unit
R _{th (j-a)}	Junction-ambient*	300	°C/W

^{*} On infinite heatsink with 4mm lead length

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ELECTRICAL CHARACTERISTICS

STATIC CHARACTERISTICS

Symbol		Test Condition s	3	Min.	Тур.	Max.	Unit
V_{BR}	Tj = 25°C	$I_R = 100 \mu A$		30			V
V _F *	T _j = 25°C	$I_F = 200 \text{mA}$	All Types			1	V
	T _j = 25°C	$I_F = 10mA$	BAT 42			0.4	
	T _j = 25°C	$I_F = 50 \text{mA}$				0.65	
	T _j = 25°C	$I_F = 2mA$	BAT 43	0.26		0.33	
	T _j = 25°C	I _F = 15mA				0.45	
I _R *	T _j = 25°C		V _R = 25V			0.5	μА
	T _j = 100°C					100	

DYNAMIC CHARACTERISTICS

Symbol	Test Condition s	Min.	Тур.	Max.	Unit
С	$T_j = 25$ °C $V_R = 1$ V $f = 1$ MHz		7		pF
trr	$T_{\rm J} = 25^{\circ} { m C}$ $I_{\rm F} = 10 { m mA}$ $I_{\rm R} = 10 { m mA}$ $I_{\rm rr} = 1 { m mA}$ $R_{\rm L} = 100 { m \Omega}$			5	ns
h	$T_j = 25^{\circ}C$ $R_L = 15K\Omega$ $C_L = 300pF$ $f = 45MHz$ $V_i = 2V$	80			%

^{*} Pulse test: $t_p \le 300 \mu s$ $\delta < 2\%$.

Figure 1. Forward current versus forward voltage at different temperatures (typical values).

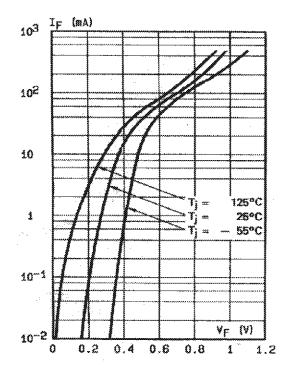


Figure 2. Forward current versus forward voltage (typical values).

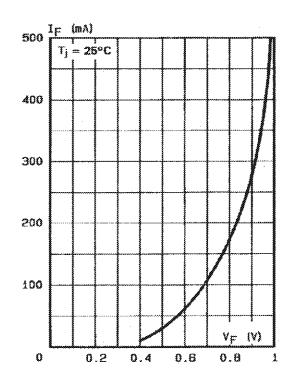


Figure 3. Reverse current versus junction temperature (typical values).

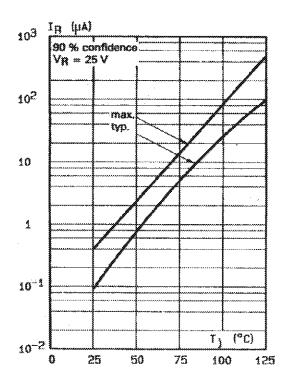


Figure 4. Reverse current versus continuous reverse voltage.

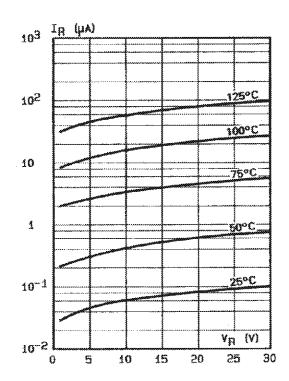
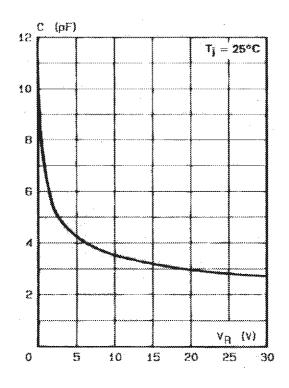
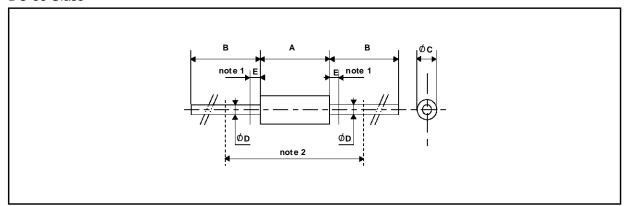


Figure 5. Capacitance C versus reverse applied voltage $V_{\mbox{\scriptsize R}}$ (typical values).



PACKAGE MECHANICAL DATA

DO 35 Glass



	DIMENSIONS						
REF.	Millimeters		Inches		NOTES		
	Min.	Max.	Min. Max.				
Α	3.050	4.500	0.120	0.117			
В	12.7		0.500		1 - The lead diameter Ø D is not controlled over zone E		
ØC	1.530	2.000	0.060	0.079	2 - The minimum axial lengh within which the device may be placed		
ØD	0.458	0.558	0.018	0.022	with its leads bent at right angles is 0.59"(15 mm)		
Е		1.27	·	0.050			

Cooling method: by convection and conduction Marking: clear, ring at cathode end. Weight: 0.15g

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